

Nano Sensors

PhD/ MTech/ BTech
Course No.: EEL7450
L-T-P [C]: 3-0-0 [3]

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Lecture 18 dated 18th Feb. 2025

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Scanning Probe Microscopy (SPM)

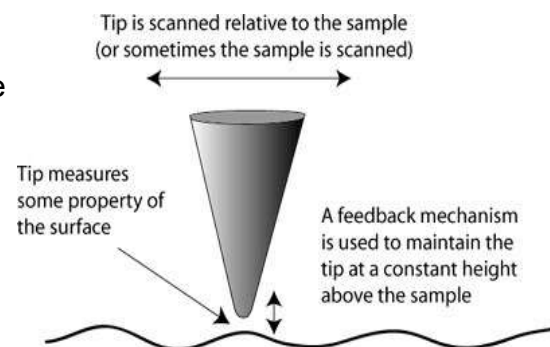
- Scanning Probe Microscopy is used to image surfaces at the nanometer scale.
- A family of microscopy forms where a sharp probe is scanned across a surface and some tip/ sample interactions are monitored.

- **Basic idea of scanned probe techniques:**

- Monitor the interactions between a probe and a sample surface

- **Two Types of SPM Microscopes:**

- Scanning Tunneling Microscope STM
- Atomic Force Microscope AFM



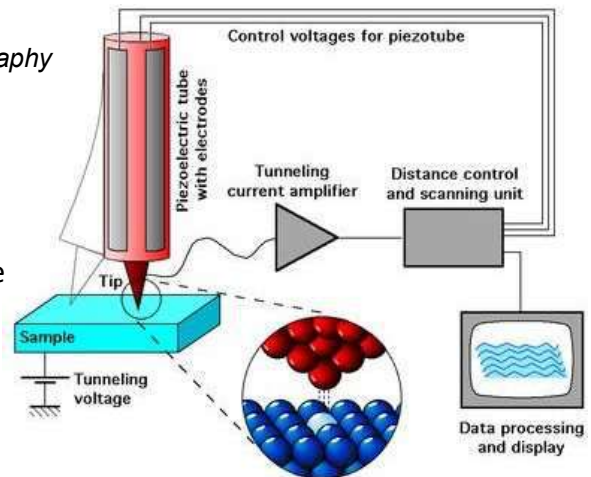
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Scanning Tunneling Microscope (STM)

➤ Technique that allows the topographic information(image) of **conducting surfaces** down to the atomic scale.

How It Works?

- It allow us to see the image of Surface topography
- The STM works by **scanning a very sharp metal wire tip** over a surface.
- By **bringing the tip very close** to the surface, and by **applying an electrical voltage** to the tip or sample, we can image the surface at an extremely small scale – down to resolving individual atoms.
- This is done by measuring tunneling current.



Typical distance between tip and sample- 0.2-0.6 nm

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What is Tunneling?

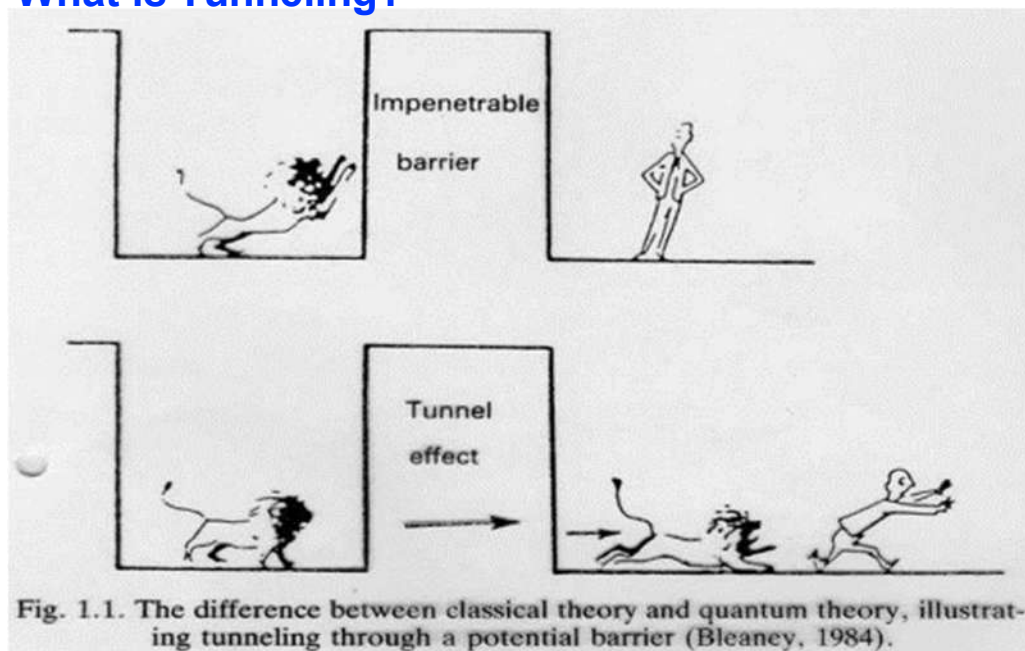
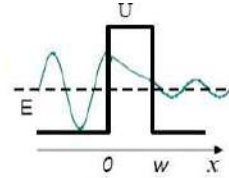


Fig. 1.1. The difference between classical theory and quantum theory, illustrating tunneling through a potential barrier (Bleaney, 1984).

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Electron Tunneling Through a barrier

The wave equation is $-\frac{\hbar^2}{2m} \frac{d^2\psi}{dx^2} + U(x)\psi = E\psi$



In the region $x < 0$, before barrier, $U = 0$, the eigenfunction is a linear combination of plane waves traveling to the right and to the left with energy $E = \frac{\hbar^2 K^2}{2m}$

$$\psi_1 = Ae^{iKx} + Be^{-iKx}$$

In the region $0 < x < w$, within the barrier, the solution is

$$\psi_2 = Ce^{Qx} + De^{-Qx} = \psi_1(0)e^{-\kappa x}; \text{ where } U_0 - E = \frac{\hbar^2 Q^2}{2m} \text{ and } \kappa = \frac{\sqrt{2m(U-E)}}{\hbar}$$

In the region $x > w$, behind the barrier, the solution is

$$\psi_3 = Fe^{iKx} + Ge^{-iKx}$$

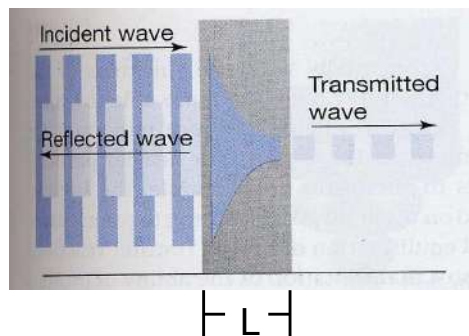
Probability of finding electrons on the other side of the barrier, i.e. **tunneling current**

$$|\psi_1(0)|^2 e^{-2\frac{\sqrt{2m(U-E)}}{\hbar} w}$$

Tunneling current scales exponentially with the barrier width

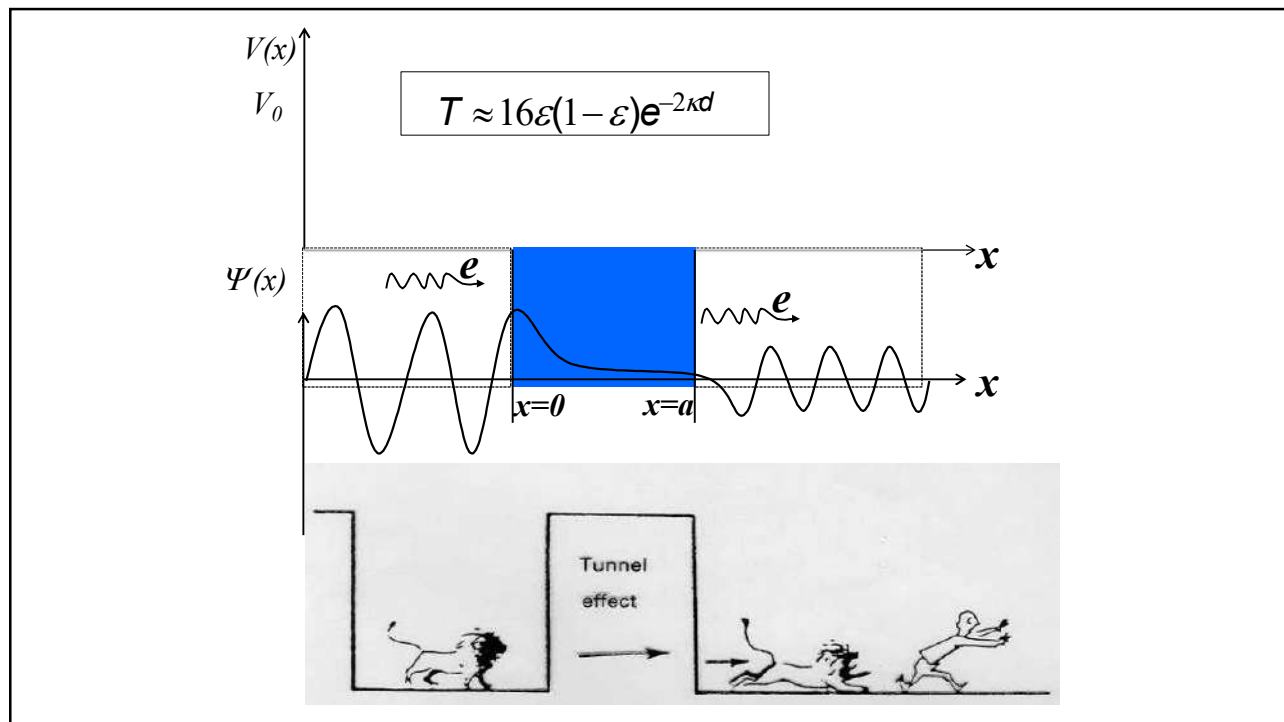
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Quantum Mechanical Tunneling



- Quantum mechanics allows a small particle, such as an electron, to overcome a potential barrier larger than its kinetic energy.
- Tunneling is possible because of the wave-like properties of matter.
- Transmission Probability: $T = ?$

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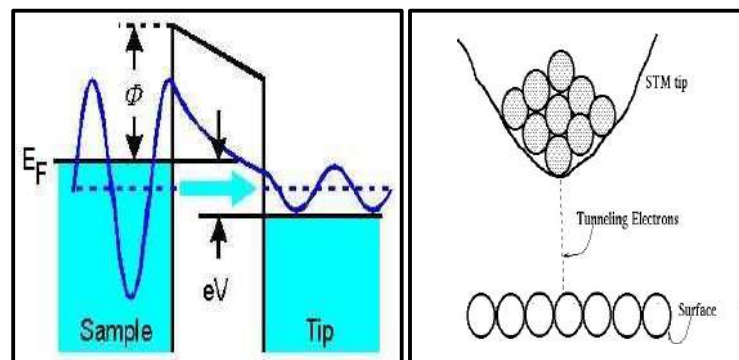
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Principle of operation:

- The STM is based on principle of quantum mechanical tunneling effect
- Monitor the tunneling current between a probe tip and a sample surface

Electron Tunneling:

In **scanning tunneling microscopy** a **small bias voltage V** is applied so that due to high electric field between tip and sample, the tunneling of electrons results in a tunneling current I .



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Principle of operation:

- **Tunnelling current** depend on **thickness of the barrier** whereby **Tip–Sample distance** ($<1\text{nm}$)
- By **monitoring the current through the gap**, we have **very good control** of the **tip-sample distance**.

Piezoelectric Tube scanner:

- **Piezoelectric tube scanner**: Piezoelectric materials are used to create a tube scanner.
- These can be used to **manipulate** an object in **three dimensions** under electronic control
- **Piezoelectric Effect** Certain materials exhibit what is called the piezoelectric effect. This is an effect whereby applying a voltage across a piezoelectric crystal, it will elongate or compress (the size of the object changes)
- **Piezoelectric Effect PZT**: Lead zirconium titanate is one of the most common piezoelectric material used.

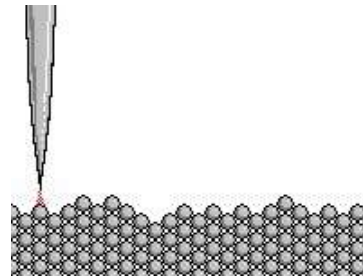
Feedback loop attached with a Display:

- Lastly, a feedback loop is required, which monitors the tunneling current and coordinates the current and the positioning of the tip.

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Two Operating modes of STM:

- **Constant Current mode**
- **Constant Height mode**



Constant Current Mode :

If the **tunneling current** is kept **constant** the **Z position of the tip** must be moved **up and down**. If this movement is recorded then the topography of the specimen can be imaged.

Constant Height Mode :

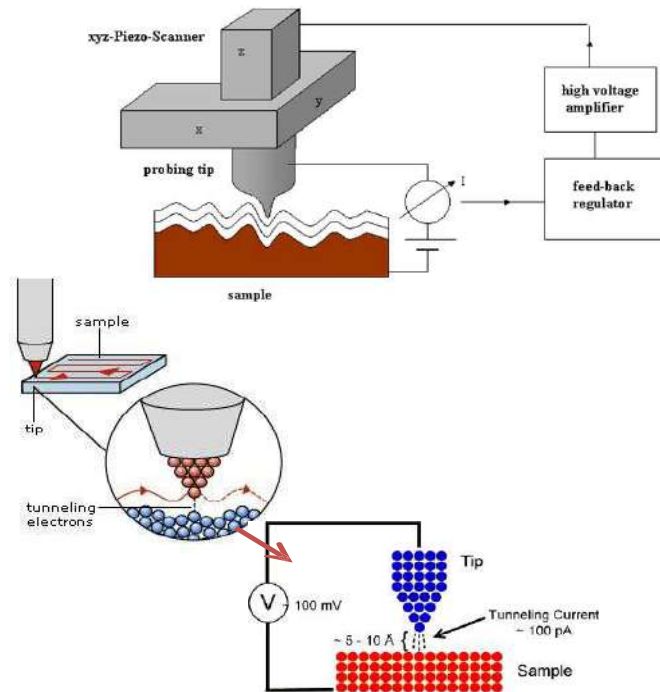
Alternatively, if the **Z position of the tip** is kept **constant** the **tunneling current** will **change** as it moves across the surface. If the changes in current are recorded, then the topography of the specimen can be imaged.

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Two Operating modes of STM:

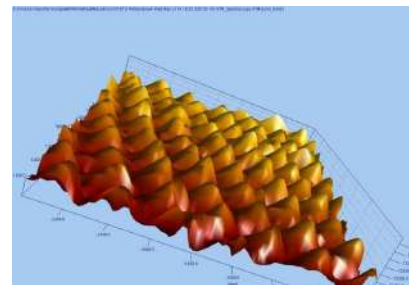
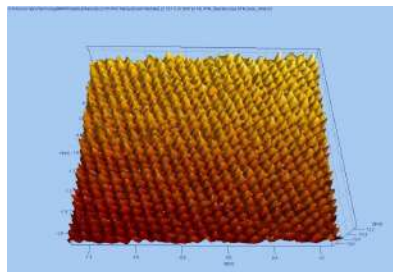
Constant Current Mode:

- In STM, a conductive tip is positioned above the surface of the sample.
- When the tip moves back and forth across the sample surface at very small intervals, the **height of the tip is continually adjusted** to keep the **tunneling current constant**.
- The height of the tip attached to XYZ **piezo scanner** is adjusted with the help of feedback loop that monitors the tunneling current continuously.
- The tip positions (Z movement) are used to construct a topographic map of the surface.

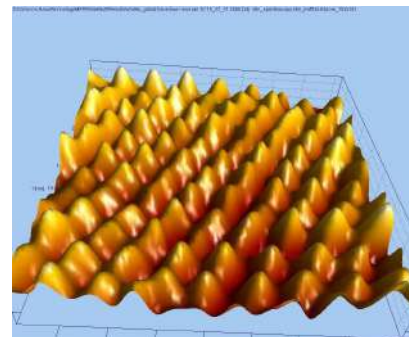
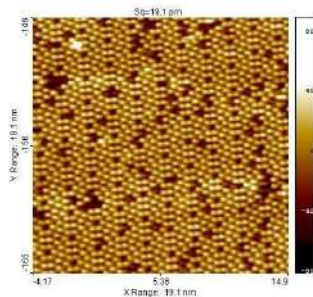


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STM Topography of HOPG



STM images of Si (111) and Au



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STM Advantages & Disadvantages

Advantages

- Used to image only conductors and semiconductors
- Able to obtain very high-resolution images
(Scanning resolution is $\sim 0.01\text{nm}$ in XY directions and 0.002 nm in Z directions, offering true atomic resolution three-dimensional image)
- Probe tips can be made out of conducting wire.

Disadvantages

- STM does not work with insulating materials
(If there are insulating materials present on the sample you can crash the tip)
- Often need to be used under vacuum

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Questions / Discussions

<https://www.youtube.com/watch?v=FQzUrbKTLVU>

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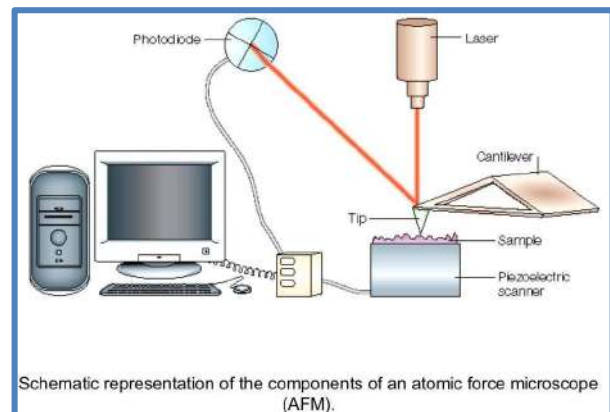
Lecture 19 dated 25th Feb. 2025

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Atomic Force Microscope AFM

- An atomic force microscope (AFM) creates a highly magnified three-dimensional image of a surface.
- AFM has the advantage of imaging almost **any type of surface**, including polymers, ceramics, composites, glass, & biological samples such as proteins and DNA.
- In an AFM, the **force** between the **sample and tip** is **detected**, rather than the **tunneling** current.
- **Determine the roughness of a sample surface or to measure the thickness of a thin layers**

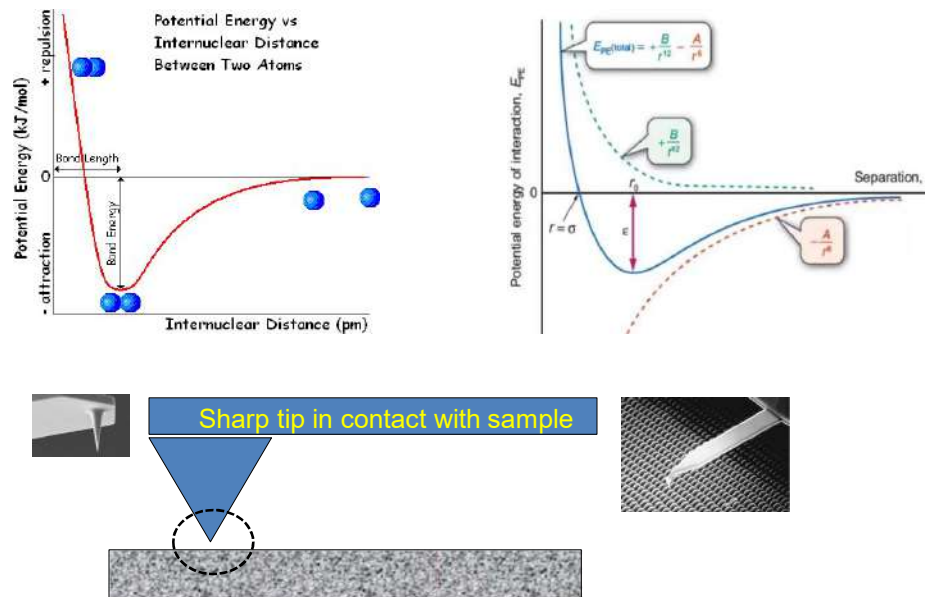
<https://www.youtube.com/watch?v=s6KqJS1GZNE>



Tip radius ~ 2 ... 50 nm
Force ~ 0.01 nN ... 1 nN
Sample: nearly any sample

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Lennard-jones potential



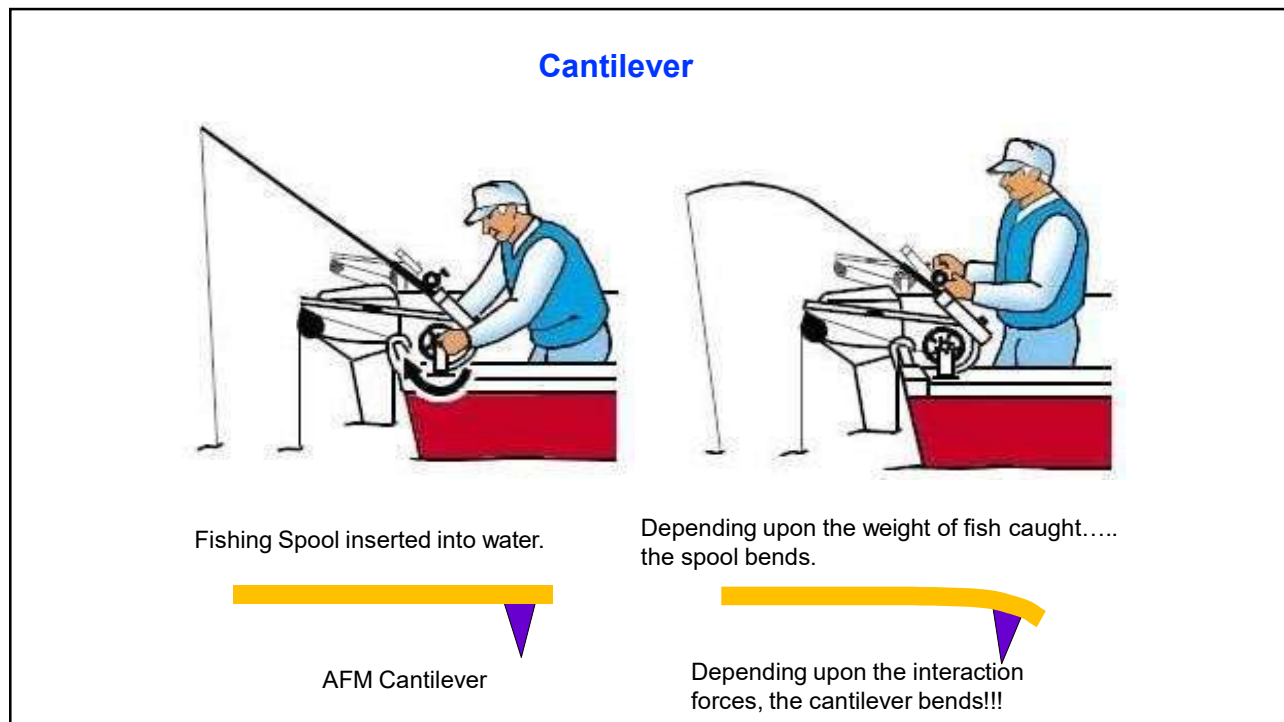
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Invented in 1986.
Binnig, Quate & Gerber.

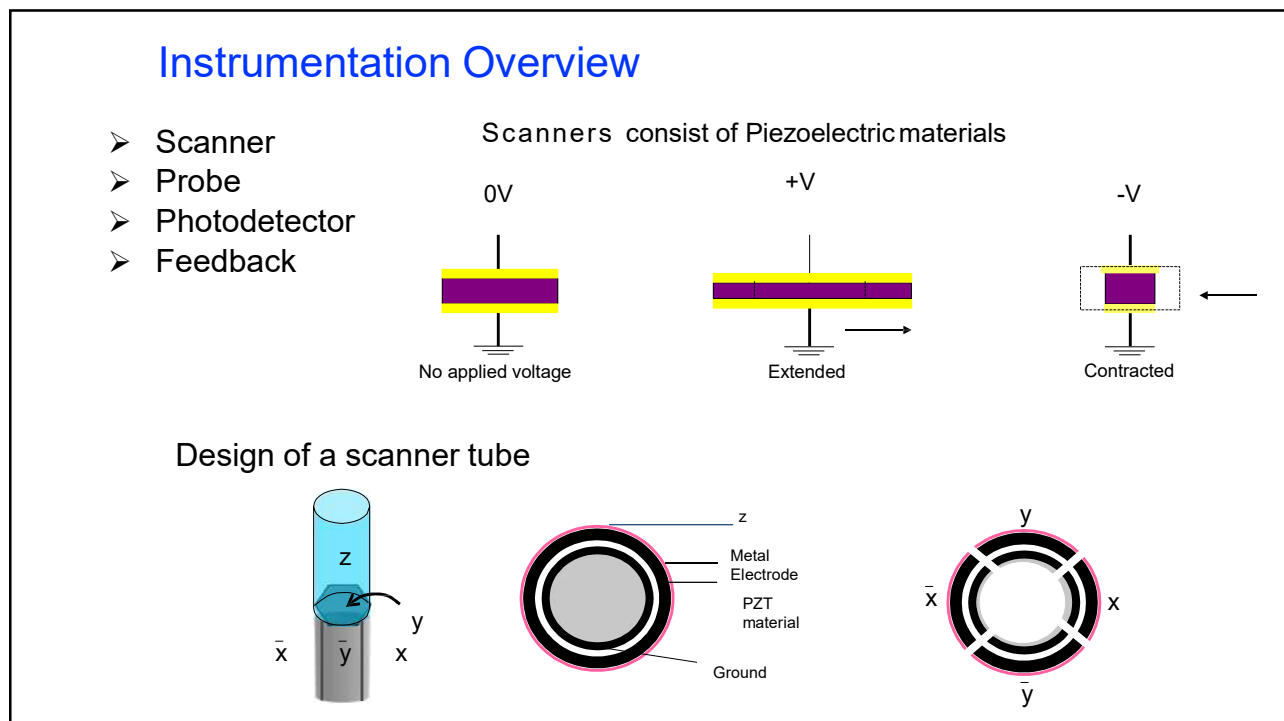
Digital Instrument's
AFM Set-up



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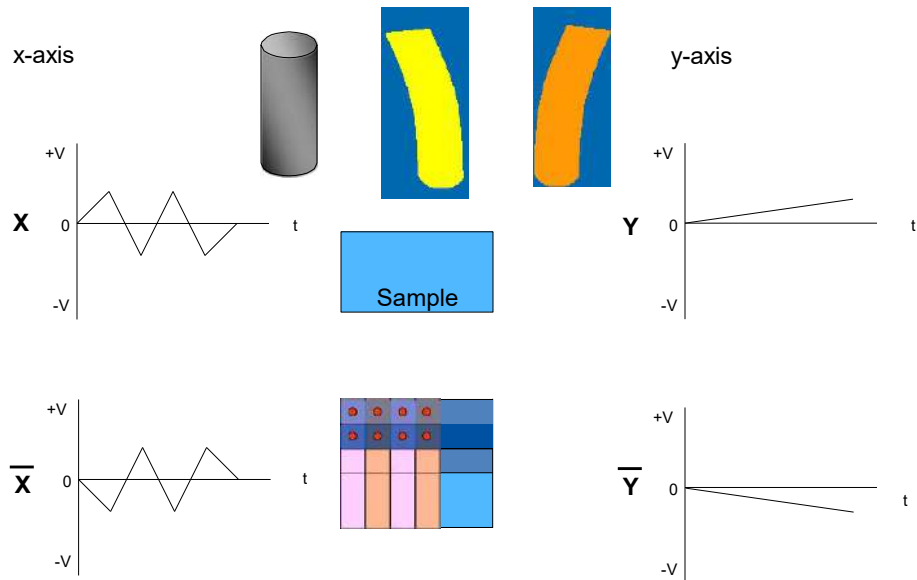


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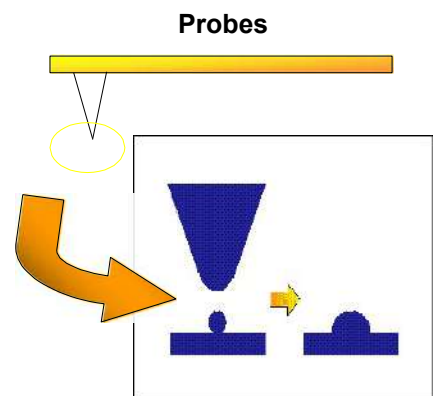
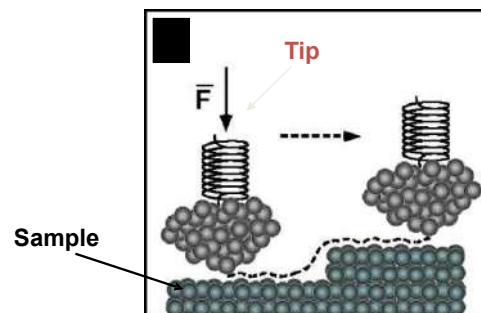
AC voltages applied at different segments of scanner tube



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There is a reflective coating at the back side of the cantilever.

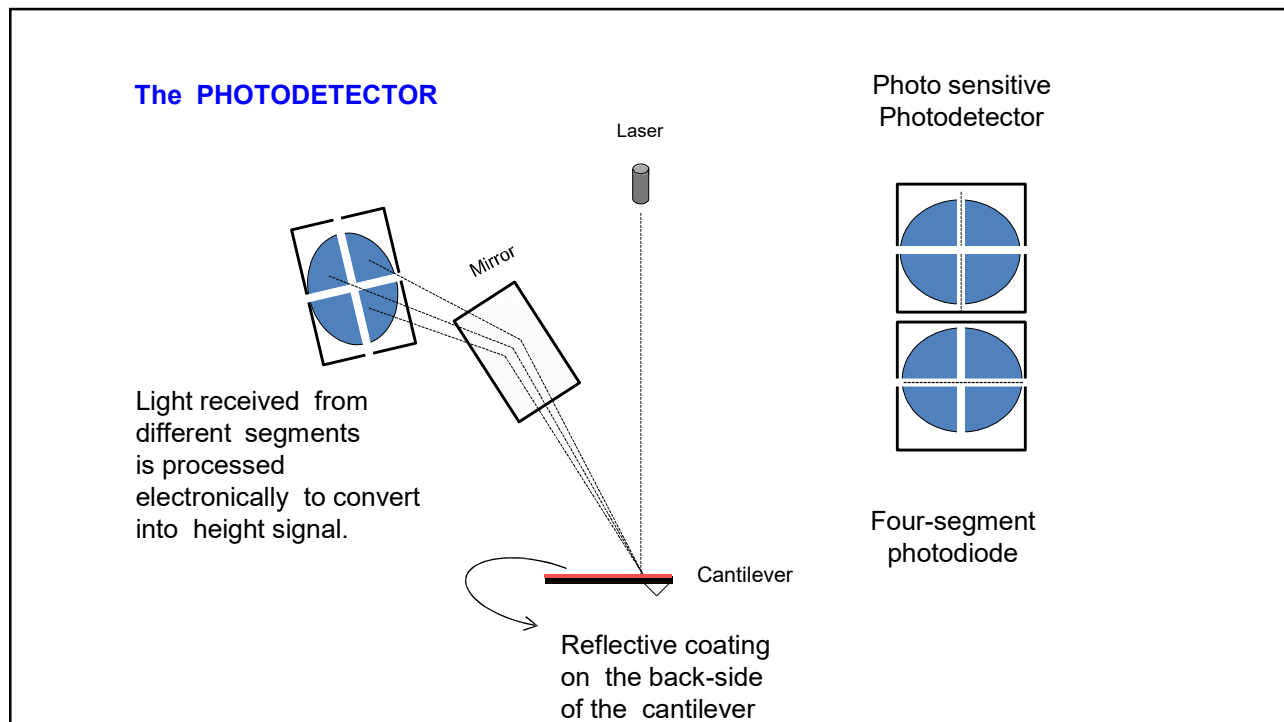
The cantilever moves on the sample surface. It follows the contours on the sample i.e. bumps or pits present on the surface.



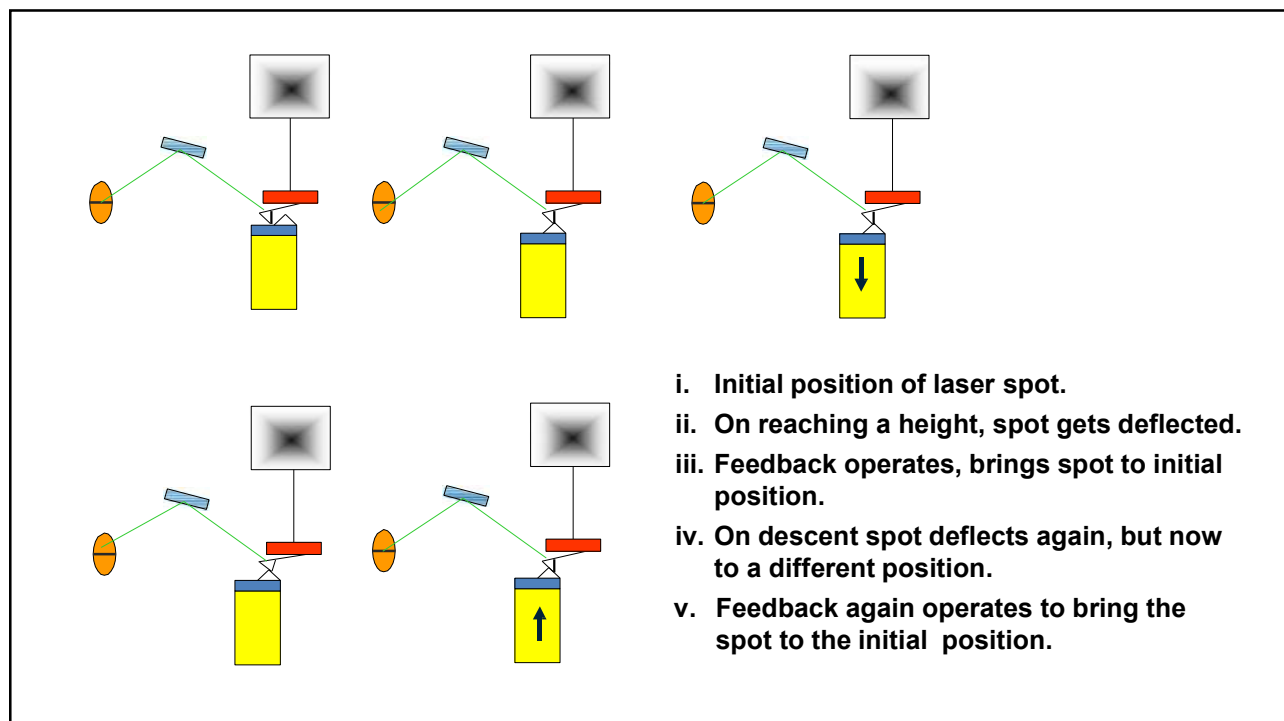
Usually Si or Si_3N_4 tips are used.

The cantilevers obey Hooke's law for small displacements. So, the interaction force between tip and sample can be found out.

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Nano Sensors: Lab sessions

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Class 20-21 dated 27-28th Feb 2025

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Nano Sensors

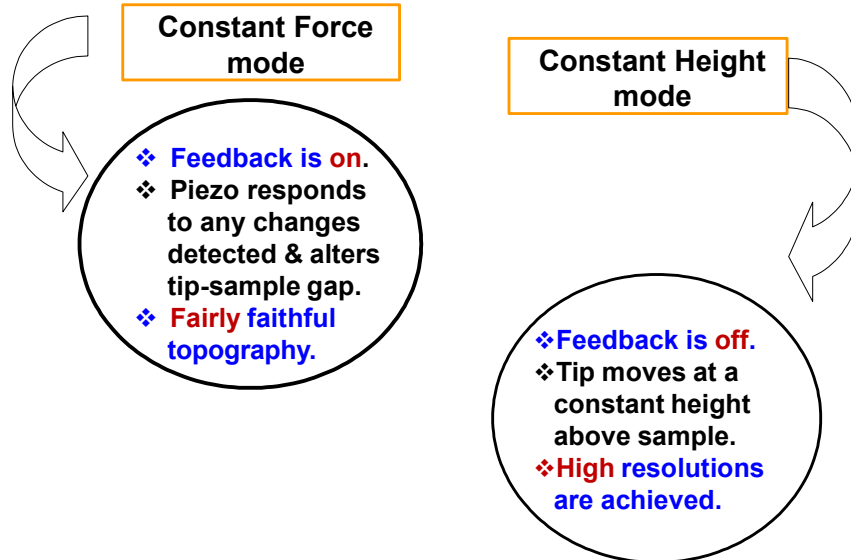
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Lecture 22 dated 4th Mar 2025

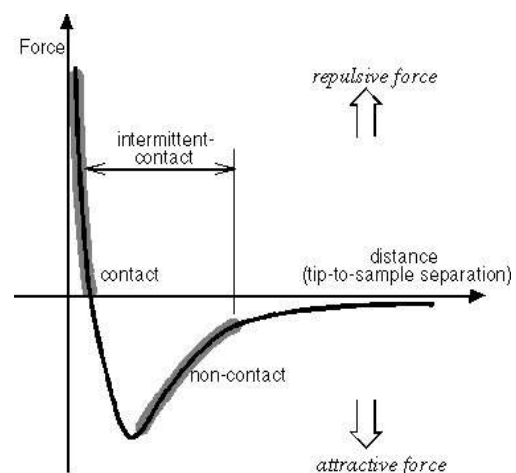
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AFM: Feedback



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- At distances few Å apart attractive van der Waals forces act between the atoms of the tip and the sample.
- When the tip approaches closer and electron clouds repel each other the attractive van der Waals forces decrease in strength.
- When the two forces balance each other at distances ~ chemical bond, the force goes to zero.



A general Force-distance curve

REGIME OF CONTACT
MODE AFM

➤ At even closer distances repulsive van der Waals forces come into play.

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AFM's Most Common Operating Modes

Contact Mode

- Tip-sample remain close while scanning.
- Mode is in the repulsive regime of force-plot.
- Large lateral forces exist- causing tip to drag.
- Strong repulsive forces act.

TAPPING Mode

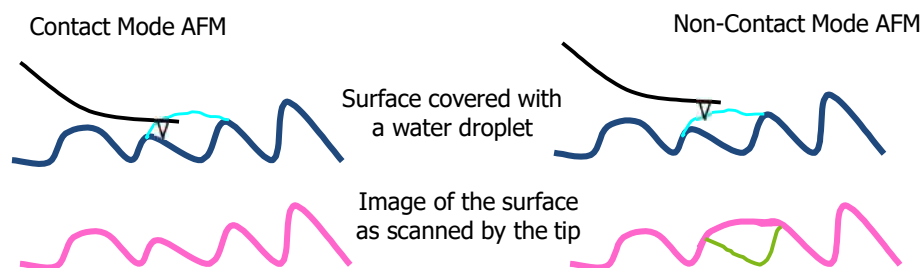
- Cantilever oscillates at/near its resonance frequency.
- Tip taps the surface occasionally.
- Lateral forces are dramatically reduced.
- Better for softer samples.

NON-Contact Mode

- Cantilever vibrates near the surface of the sample.
- No physical contact with sample surface.
- Changes in resonant freq, vibration amplitude are detected.
- Cantilevers used are stiffer.

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Difference between Contact and Non-contact Mode

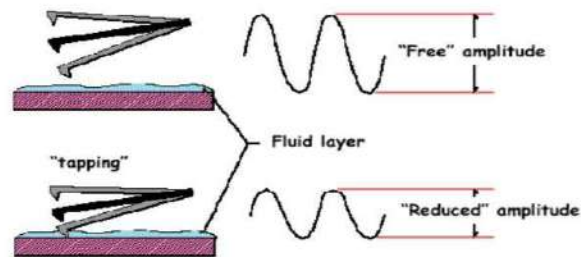


- Tapping mode provides the best resolution.
- The lateral forces present in the contact mode are dramatically reduced in this mode giving a higher lateral resolution.

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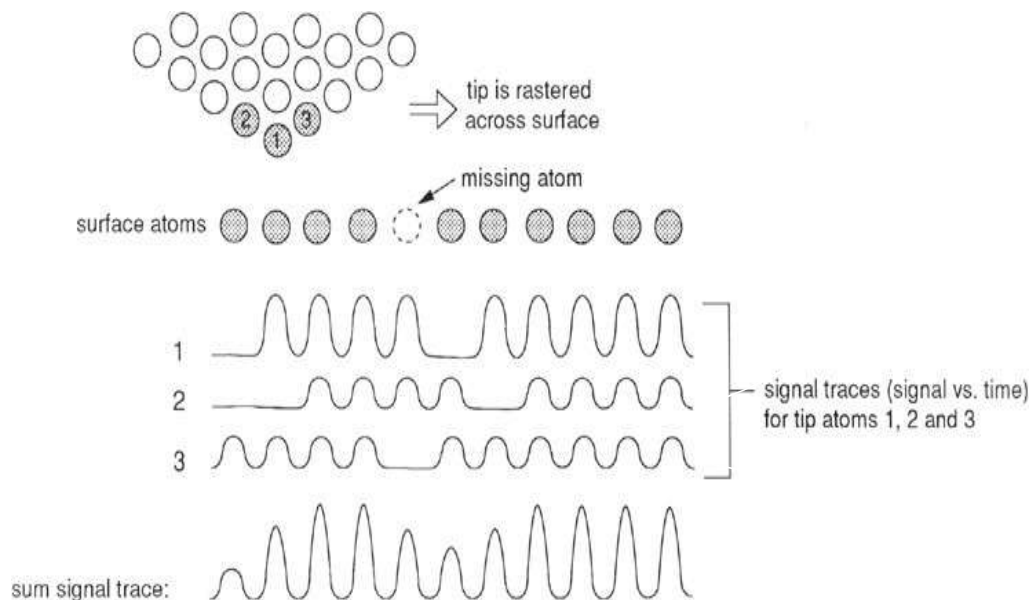
Non-contact vs. tapping mode

- Both are based on a Feedback Mechanism of constant oscillation amplitude.
- Non-contact mode: amplitude set as $\sim 100\%$ of "Free" amplitude;
- Tapping mode: amplitude set as $\sim 50 - 60\%$ of "Free" amplitude.
- Tapping mode provides higher resolution with minimum sample damage.
- **Most of times, non-contact mode is operated as tapping mode.**



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Effect of Tip-Shape on Imaging



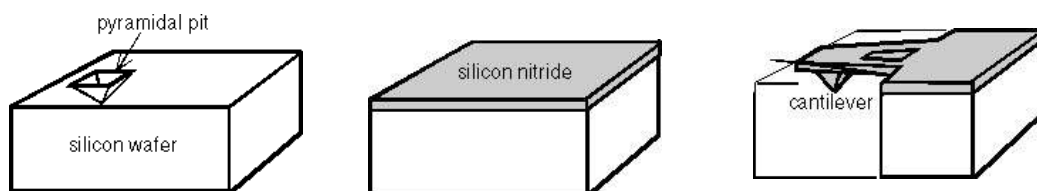
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1. Silicon tips:

- Silicon conical tips are made by etching into the silicon around a silicon dioxide cap.
- They high aspect ratio but they may break more easily than the pyramidal or tetrahedral geometries.

2. Silicon nitride tips

- SiN tips are fabricated by depositing a layer of silicon nitride over an etched pit in a crystalline silicon surface as shown in the figure.
- Silicon nitride is a harder material than silicon, which also makes silicon nitride tips more durable than silicon tips.

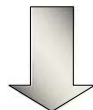


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Some Facts

- Typical forces between probing tip and sample range from 10^{-11} to 10^{-6} N.
- The interaction between **two covalently bonded atoms** is of the order of 10^{-9} N at separations $\approx \text{\AA}$.
- In non-contact mode the separation between tip & sample ~ 10 to 100 nm.
- van der Waals, electrostatic, magnetic or capillary forces are into play.
- At smaller separations $\sim \text{\AA}$ the probing tip is in contact with the sample.

Here, ionic repulsion forces allow the surface topography to be traced with high resolution.

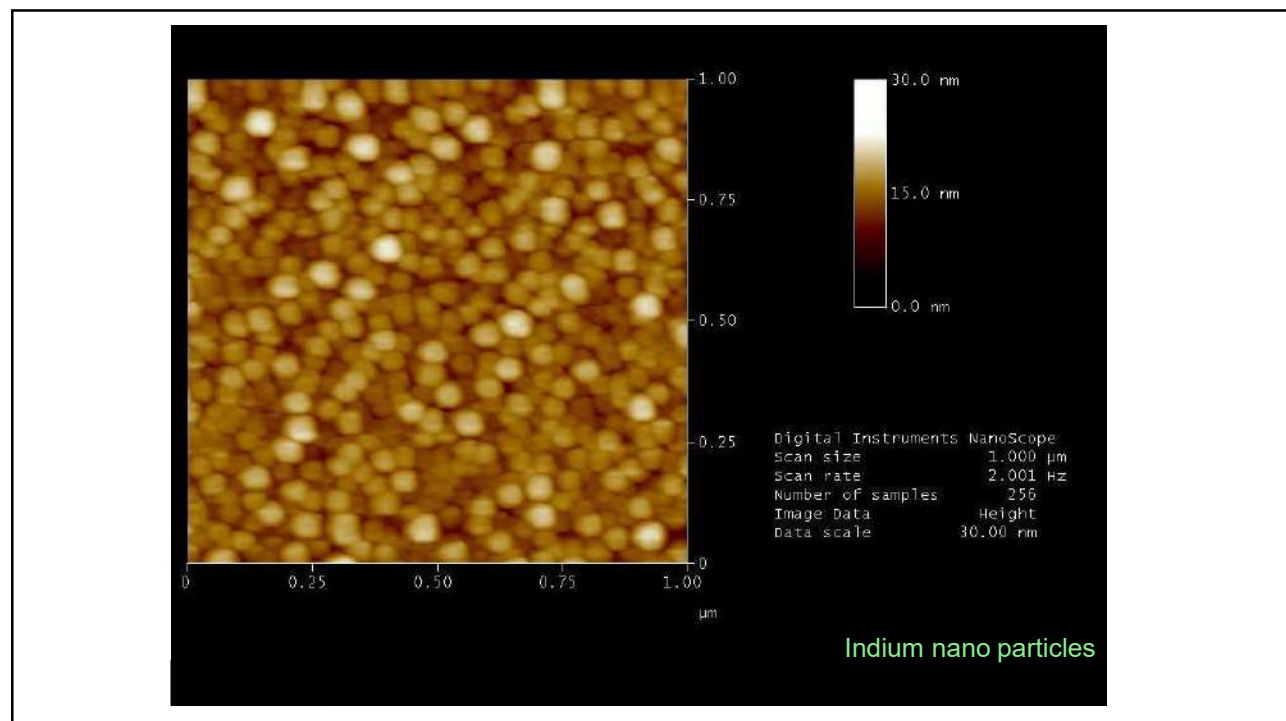


This results in a higher resolution for imaging in contact mode.

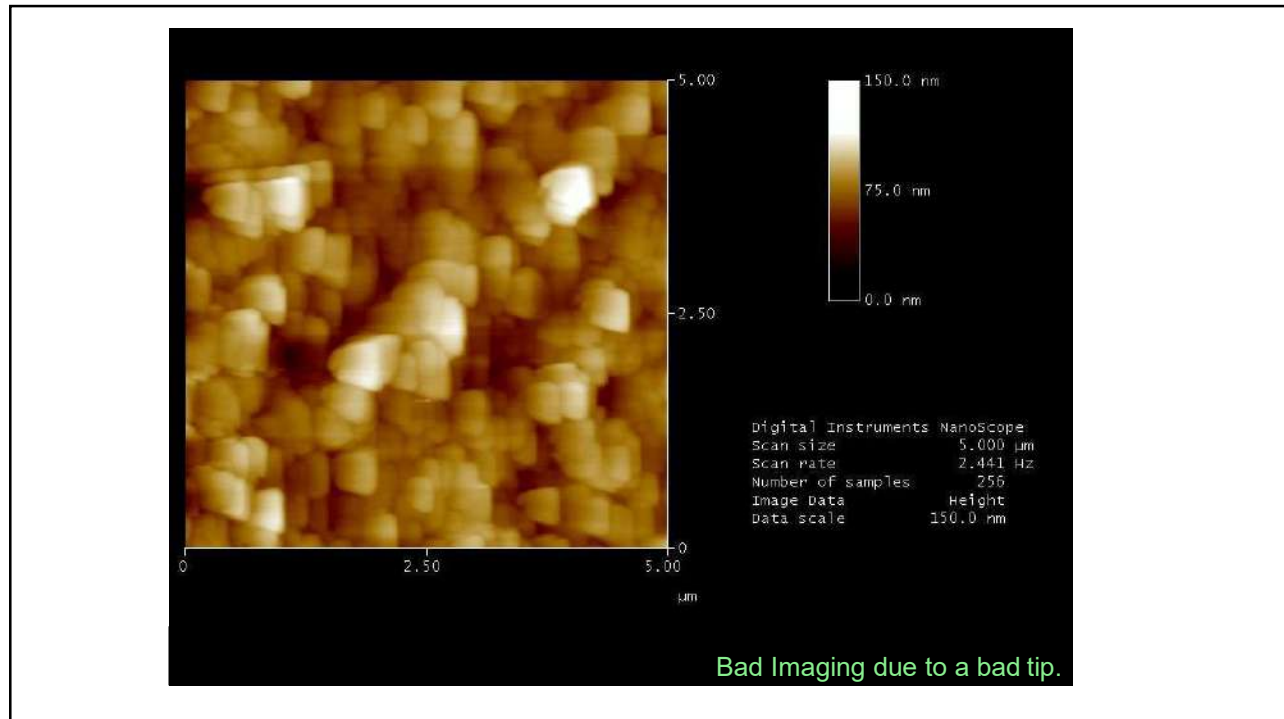
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Some Images ...

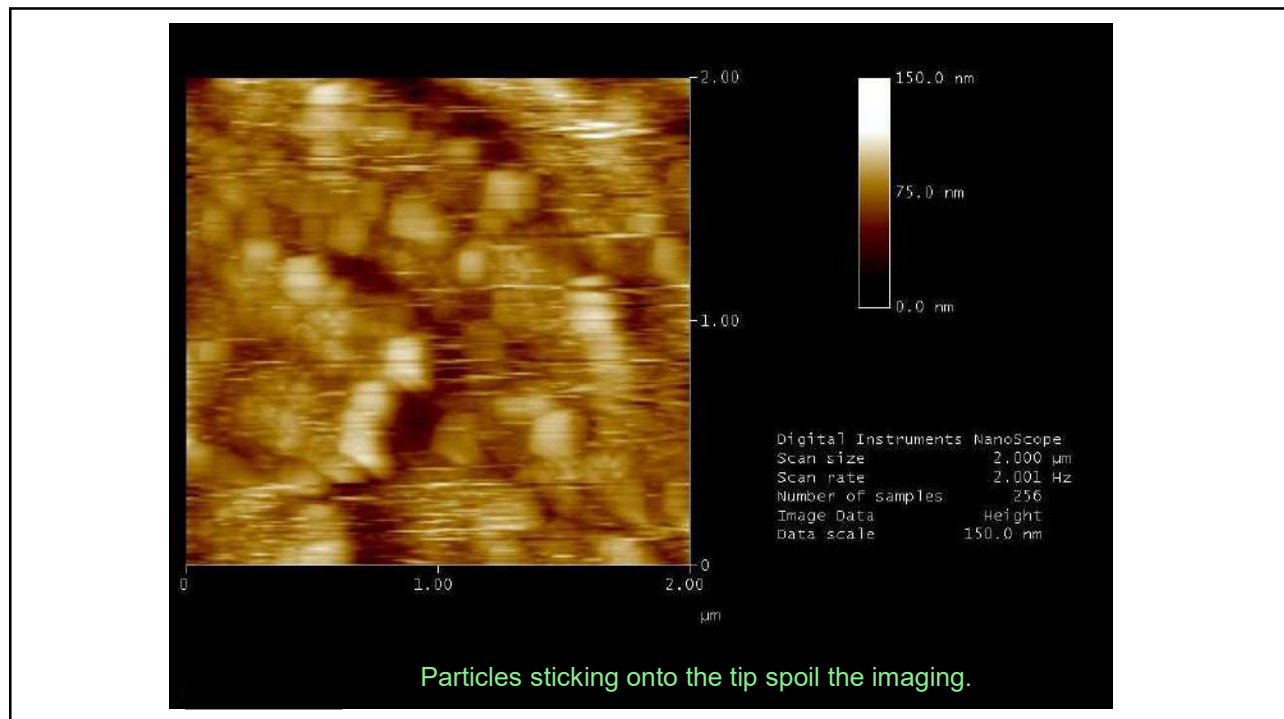
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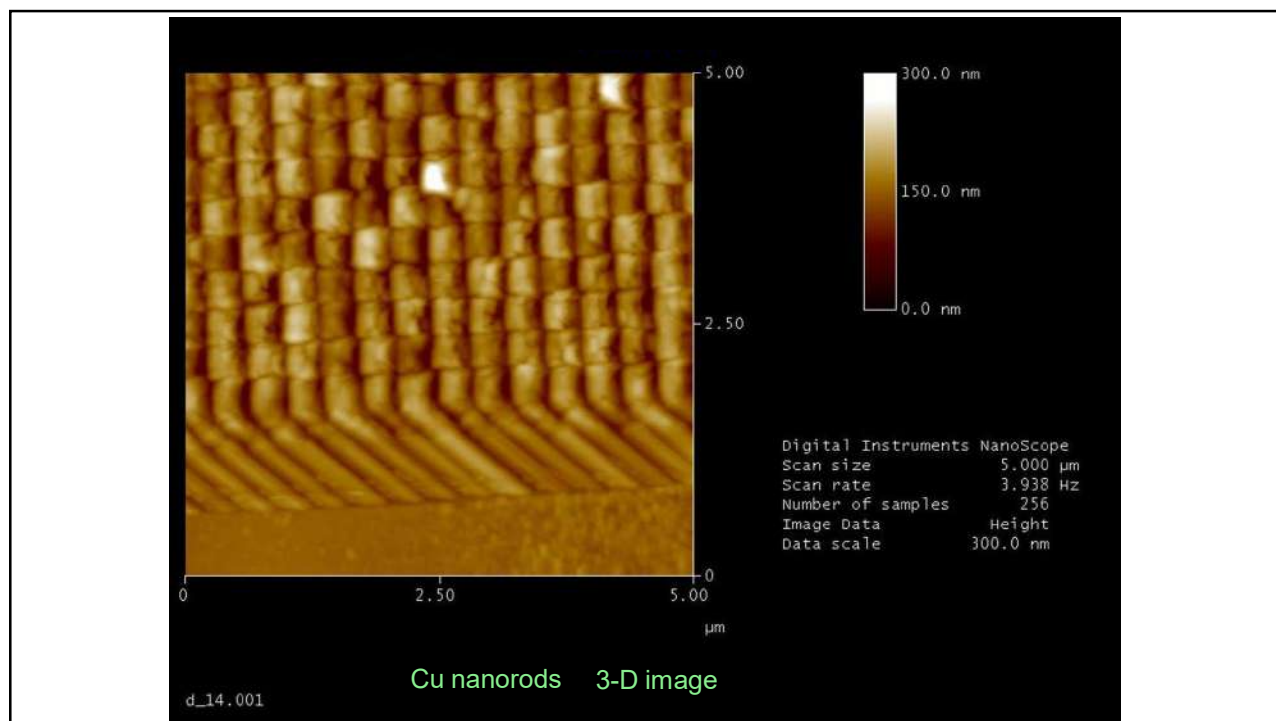
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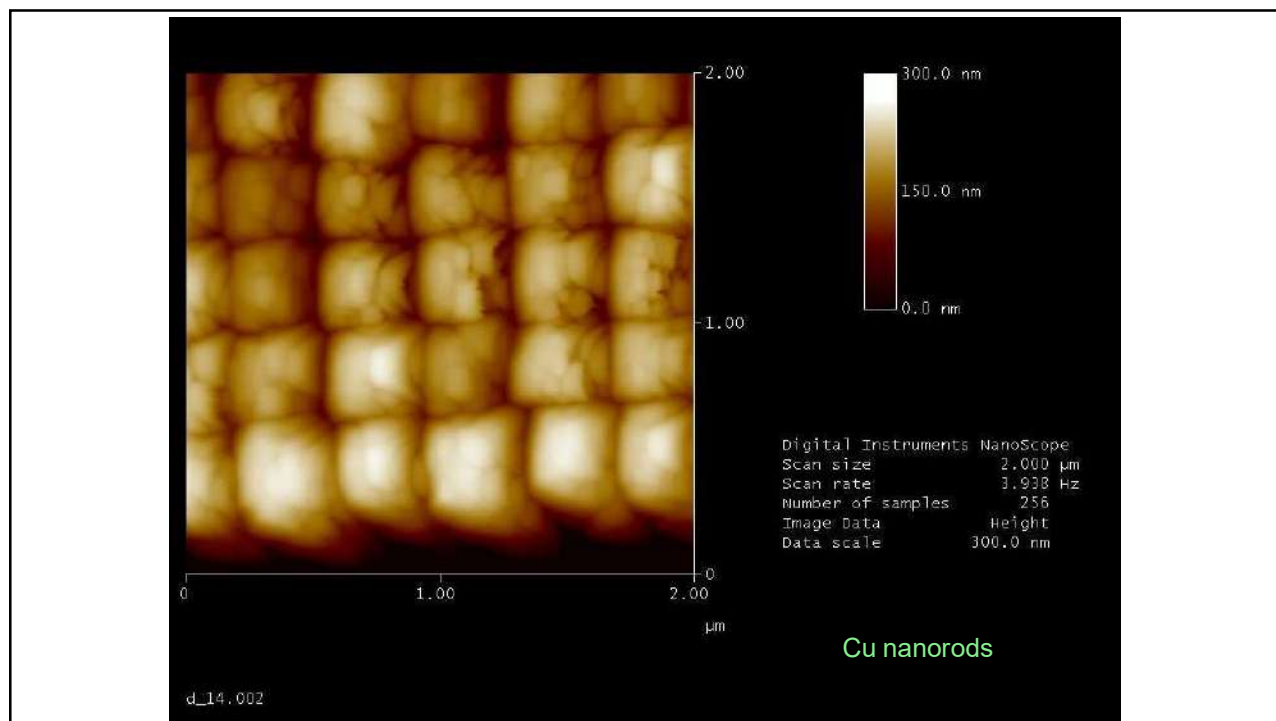
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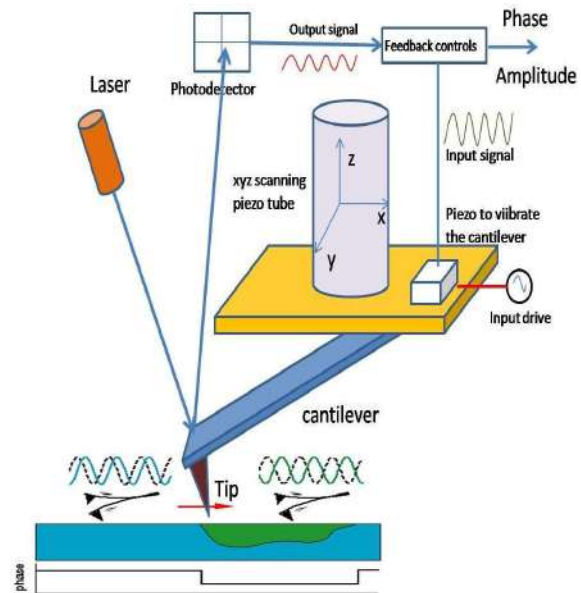
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Phase Imaging

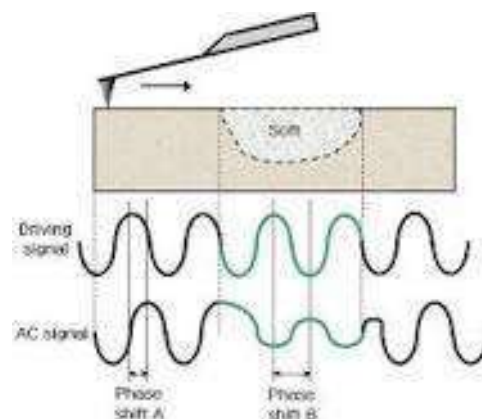
- **Phase image**: The phase lag of the cantilever **oscillation**, relative to **drive** signal
 - Simultaneously imaged with topography
- Phase lag is dependent on factors such as: **viscoelastic properties** of the surface, **composition**, **adhesion** and **friction**
- Helpful in identifying multi-phase morphology of polymer blends



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Phase Imaging

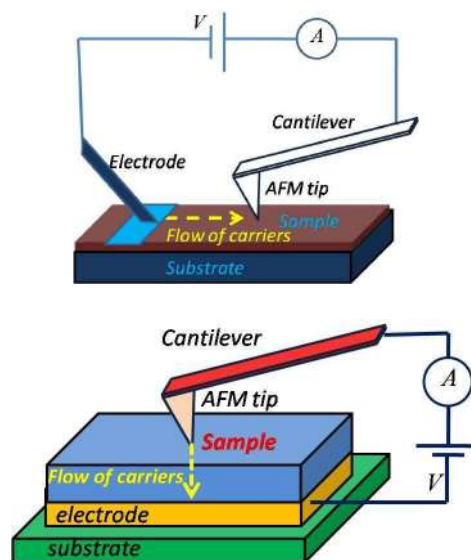
- Phase Imaging refers to the monitoring of the phase lag between the **signal that drives the cantilever oscillation** and its **output signal** as shown in Figure.
- **Changes in the phase lag** reflect changes in the **mechanical properties** of the sample surface.



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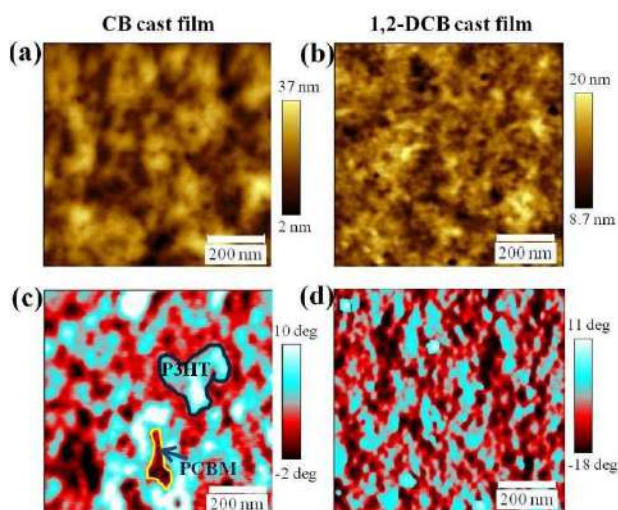
Current sensing - AFM

- CS-AFM measures the **local electrical conductivity** of a material at nanoscale
- **Current flow direction** in the sample can be controlled: either **lateral** or **transverse** direction through appropriate electrode configuration
- Local Electron/ hole mobility can be estimated from local I-V plots
- Local photocurrent can be measured by conducting I-V spectroscopy under light illumination



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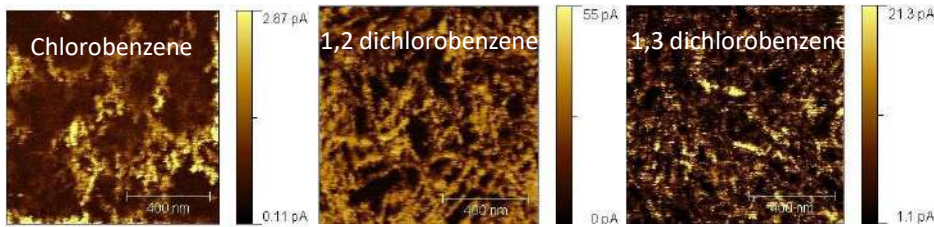
Topography and phase imaging



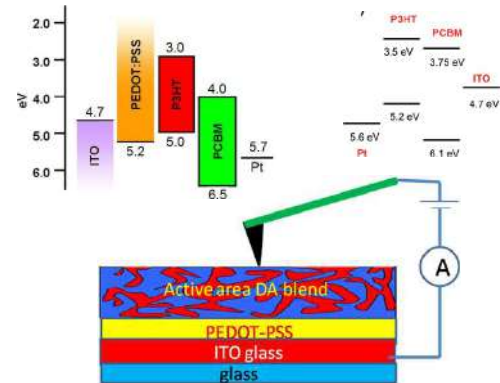
Topography images of poly(3-hexylthiophene): phenyl- C_{61} -butyric acid methyl ester (P3HT:PCBM) blended films spin cast from CB & 1,2-DCB solvents, respectively. (c and d) shows the corresponding phase images

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Current Sensing-AFM

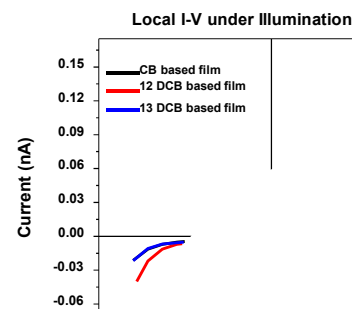
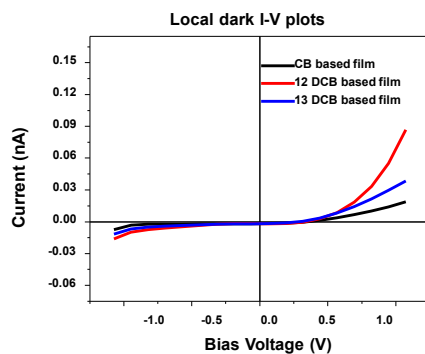


- Brighter regions (higher hole current) correspond to P3HT
- Darker regions (lower hole current) correspond to PCBM
- Nanoscale charge transport pathways are clearly defined in 1,2 DCB film, which also has higher electrical conductivity as compared to CB & 1,3 DCB films

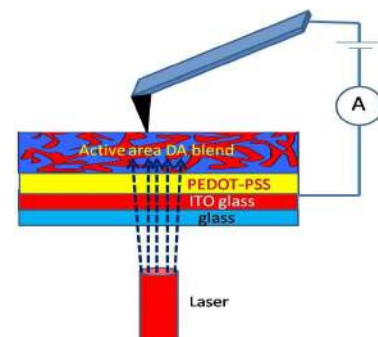


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Local I-V measurements by CS-AFM

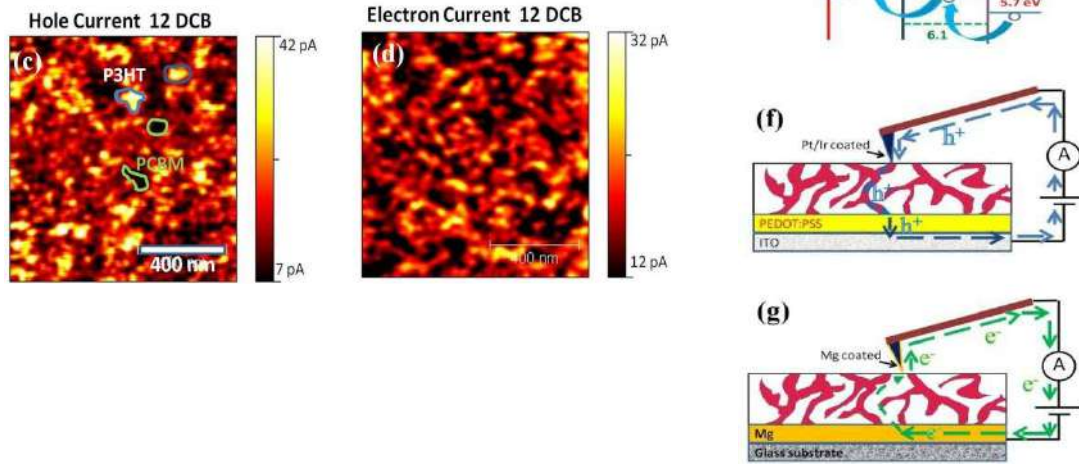


- Local I-V spectroscopy plots under dark and illuminated (680 nm, $\sim 10^{18}$ photons/cm²-sec) conditions show significant 'photo-response', despite weak absorption in RED region
- Local Current in all the films increased with illumination
- Dark current and illuminated photo-current was maximum in 1,2 DCB based film



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CS-AFM and selective carrier dynamics



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Hole mobility calculations from local I-V plots

- Space charge limited current density (SCLC)

$$J = \frac{9}{8} \epsilon \epsilon_0 \mu \frac{V^2}{L^3}$$

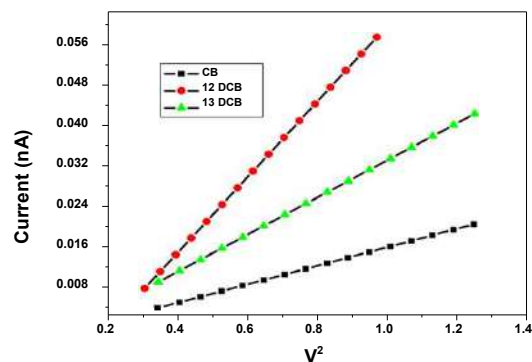
(Mott, N. F. Gurney, R. W. Electronic Processes in Ionic Crystals, Oxford University Press, London, 1948)

- Hole mobility (dark) obtained by fitting the above equation

➤ CB	$4.64 \times 10^{-3} \text{ cm}^2/\text{V-s}$
➤ 1 3 DCB	$6.89 \times 10^{-3} \text{ cm}^2/\text{V-s}$
➤ 1 2 DCB	$1.40 \times 10^{-2} \text{ cm}^2/\text{V-s}$

- Highest hole mobility in 1 2 DCB film

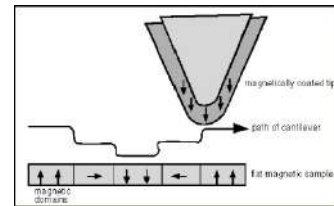
J = current density
 Tip radius = 20 nm
 ϵ = dielectric constant
 μ = hole mobility
 V = bias
 L = thickness of film



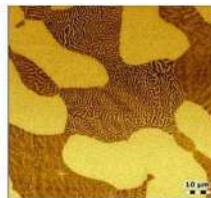
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Magnetic Force Microscopy (MFM)

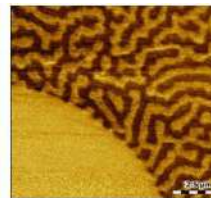
- Because the magnetic forces interact at greater distances than van der Waals forces, so electrical or magnetic force information can be separated from surface topography simply by increasing the tip-to-sample distance i.e. by lifting up the tip.
- Dual scanning:** the tip first acquires surface topography in the tapping mode, then the tip is lifted up, and retraces the surface profile maintaining constant tip-surface separation.



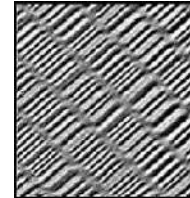
Topography of a polished stainless steel sample.
Scan size: 80 μm .
Height range: 50 nm.



Magnetic force microscopy (MFM) of the same 80 μm \times 80 μm area.
Phase range: 10°.



Magnetic force microscopy (MFM) of a smaller area.
Scan size: 13 μm .
Height range: 50 nm.



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Questions / Discussions

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